ISSN 1330–0008
CODEN FIZAE4

(Ba/Sr)O-BI-LAYER ORDERING IN THE $RE_2(Ba/Sr)_2GaCu_2O_9$ SUPERCONDUCTING CUPRATE[1]

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Received 14 February 1997

UDC 538.911, 538.945

PACS 61.10.My, 61.16.-d, 74.72.-h

This paper is dedicated to Professor A. Bonefačić on the occasion of his 70th birthday

Ordering in the (Ba/Sr/Nd)O bi-layers (of "Rock-Salt" type structure) of the $RE_2(Ba_{0.65}Sr_{0.20}Nd_{0.15})_2GaCu_2O_9$ high-T_c superconducting cuprate was investigated by electron microscopy and diffraction. Besides the average layered structure based on the tetragonal perovskite cell $a_p \times a_p \times c_p$ and the meandering chain superstructure based on the orthorhombic $4a_p \times 2a_p \times c_p$ cell in the GaO-layers, an additional ordering was found in the pairs of (Ba/Sr/Nd)O-...-(Ba/Sr/Nd)O layers. We propose a model for ordering of 3Ba and 1Sr cations on a two-dimensional $2a_p \times 2a_p$ lattice cell in each (Ba/Sr/Nd)O layer. This compositional intra-layer ordering is accompanied by the inter-layer plane stacking disorder. The 4-fold symmetry of the average tetragonal structure is preserved, while the translation parameters in the (a, b) plane are doubled. This local ordering in the RS-type bi-layers hardly affects the symmetry of the basic structure; however, it may act as a source of weak anisotropy in the CuO_2-layers.

[1]Parts of this paper have been presented at "2nd Croatian Symposium on Application of Electron Microscopy in Life Sciences and Materials Science", Zagreb, October 4, 1996.

1. Introduction

Layered structure of high-T_c superconducting cuprates (HTCSC) is anisotropic "per se"; it induces anisotropy of all physical properties such as electrical superconductivity or magnetic susceptibility. The average structure is tetragonal, while the basic structure of the prototype $YBa_2Cu_3O_{7-x}$ compound (noted also "YBCO" or "Cu-1212C" [1]) is orthorhombic. The Cu atoms in the CuO-chain layers of the Cu-1212C structure can be completely replaced [2] by the M = Ni, Ta, Ga, Co, Al, Hg, ... atoms [3-6], and even by the non-metallic C, S, P, N [7-10] atoms. These replacements hardly affect the average tetragonal structure. Various MO-chain arrangements were found to induce structural anisotropy in the form of orthorhombic superstructures with larger superlattice cells [11-14], however, with no profound effect on the anisotropy of physical properties.

In this paper, we present the results of an investigation of ordering in the (Sr/Ba/Nd)O layers of the $(Nd_{0.75}Ce_{0.25})_2(Sr_{0.20}Ba_{0.65}Nd_{0.15})_2GaCu_2O_{9+\delta}$ compound using electron microscopy and diffraction. Although the material is of a particular composition, this ordering is of general interest because the RS-type layers are present in all HTCSC structures; these layers are adjacent to both the MO-chain layers and the CuO_2-plane layers. Ordering in the RS-type layers has not been recognized so far as a significant effect in the most of HTCSC structures.

2. Structural consideration

The basic structure of the $(RE)_2(Sr_{0.20}Ba_{0.65}Nd_{0.15})_2GaCu_2O_{9+\delta}$ compound, termed here the Ga-1222C structure [15], can be represented by the layer stacking sequence in the unit slab, Fig. 1a:

$$\ldots\text{–GaO–}(Sr_{0.20}Ba_{0.65}Nd_{0.15})\text{O–}CuO_2\text{–RE–}O_2\text{–RE–}CuO_2\text{–}(Sr_{0.20}Ba_{0.65}Nd_{0.15})\text{O–}\ldots$$

The thickness of this unit slab is 1.41 nm, while the repeat distances within a slab are determined by the basic perovskite square lattice with parameters: $a_p^{(1)} \times a_p^{(2)}$ ($a_p^{(1,2)} =$ 0.39 nm). The presence of the RE-O_2-RE fluorite-like lamella causes a lateral shift over $1/2[110]_p$ of the two parts of unit slab on either side of the lamella, Fig. 1a. The repeat distance along the normal to the layers contains two unit slabs ($c_p = 2 \times 1.41$ nm), and the resulting basic lattice has a body centred tetragonal cell: $a_p^{(1)} \times a_p^{(2)} \times c_p$.

Two different arrangements were found in the GaO-chain layers of the $(RE)_2(Sr_{0.85-x}Ba_xNd_{0.15})_2GaCu_2O_{9+\delta}$ basic structure depending on x, the level of Ba-doping. For $x = 0$, the GaO-chains run diagonally along one of the two $[110]_p$ (or $[110]_p$) directions [3-5,11,12]. For $x = 0.65$, the GaO-chains meander along the principal directions $[100]_p$ (or $[010]_p$) [13,14,16]. The corresponding superstructures are based either on the $2\sqrt{2}a_p^{(1)} \times \sqrt{2}a_p^{(2)} \times c_p$, or on the $4a_p^{(1)} \times 2a_p^{(2)} \times c_p$ superlattice cell, respectively. Each GaO-chain-layer is ensandwiched by a pair of $(Sr_{0.20}Ba_{0.65}Nd_{0.15})$O layers, Fig. 1b. The $(Sr_{0.20}Ba_{0.65}Nd_{0.15})$O plane spacing within this bi-layer is $C = 0.43$ nm, while the separation between the bi-layers is much larger, 0.98 nm.

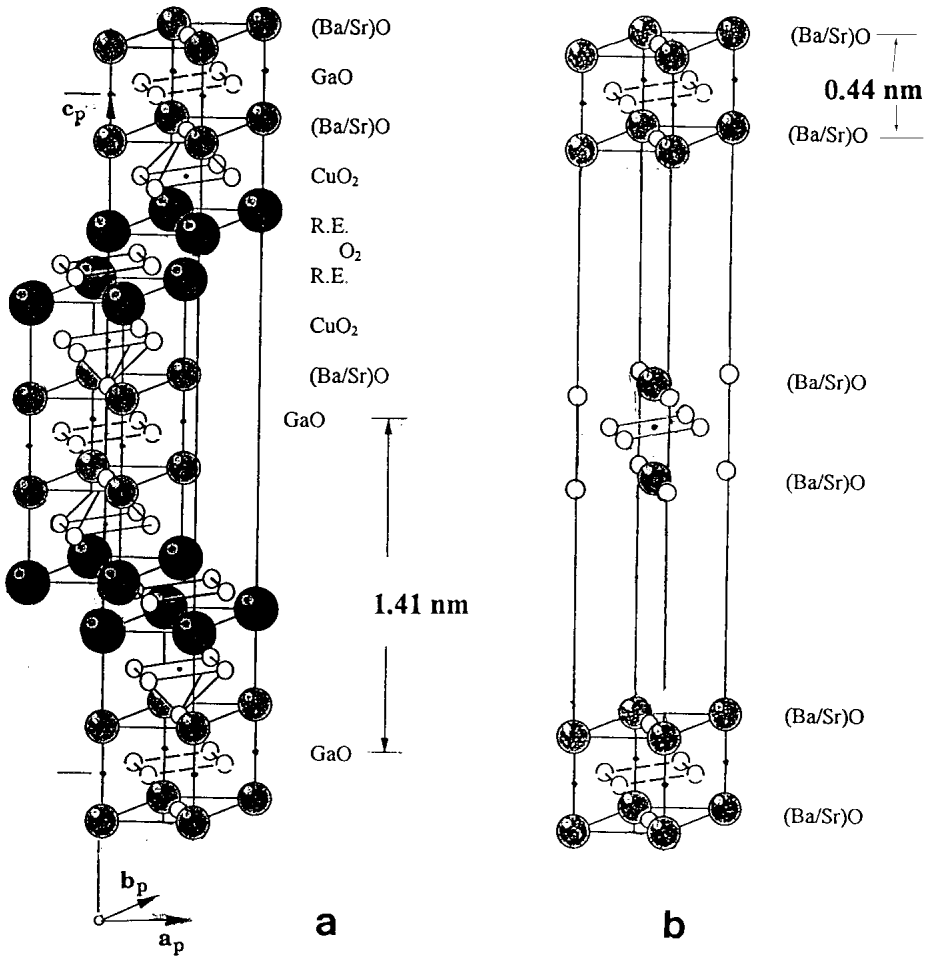

Fig. 1. Schematic representation of layered structure of $RE_2(Ba/Sr/Nd)_2GaCu_2O_9$ *compound: (a) front view of the complete structure; (b) view of the partial* (Sr/Ba/Nd)O *bi-layer structure.*

3. Electron diffraction patterns

The diffraction pattern along the [001] zone of this Ga-1222C structure is shown in Fig. 2. The series of diffraction patterns taken in the course of tilting experiment around the [001] axis are reproduced in Fig. 3. These reciprocal lattice sections provide an unambiguous reconstruction of the complete Ga-1222C structure, the GaO-chain-layer partial structure, as well as the partial structure of the RS-bi-layers.

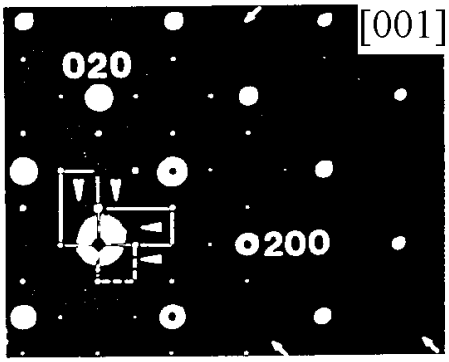

Fig. 2. EDP of the $RE_2(Sr_{0.20}Ba_{0.65}Nd_{0.15})_2GaCu_2O_9$ *compound along the* [001] *zone; four strong basic spots are marked with dots; the broken square marks the unit mesh of the* $2a_p \times 2a_p$ *lattice. The full line rectangles mark the C-centred meshes of two variants of the* $4a_p \times 2a_p$ *superlattice. Arrows at top and bottom indicate the extinctions. Arrowheads mark the spots at the points of intersections of diffuse streaks of Fig. 3.*

The most intense spots in all patterns are those generated by the basic perovskite sublattice. Due to the extinction condition, $h_p + k_p + l_p =$ odd, the basic spots can be indexed by a tetragonal face-centred reciprocal cell: $a_p^\star \approx (1/0.39)\ \mathrm{nm}^{-1}$, $c_p^\star \approx (1/2.82)\ \mathrm{nm}^{-1}$. This is in agreement with the body-centred cell of the basic Ga-1222C structure, Fig. 1a.

Besides the $d^\star_{110p} \times d^\star_{110p}$ square mesh of basic spots, marked by black dots in Fig. 2, two meshes of weak spots represent two superlattices: the square mesh of sharp spots (with reciprocal cell indicated by the dashed lines) reveals a $2a_p^{(1)} \times 2a_p^{(2)}$ plane superlattice, and two rectangular meshes (with cells marked by the full lines) indicate the $4a_p^{(1)} \times 2a_p^{(2)}$ (and $4a_p^{(2)} \times 2a_p^{(1)}$) plane superlattices which are due to the meandering GaO-chain arrangements discussed in earlier papers [13,14,16].

Besides the basic spots, the patterns in Fig. 3 consist of two different types of diffuse streaks (based on the two above mentioned plane superlattice cells):

(') the streaks marked by double arrowheads in Figs. 3a,b and d exhibit clear intensity modulation along the $c^\star$-axis. These streaks intersect the $(hk0)^\star$ reciprocal lattice section of Fig. 2 at the vertices of the $1/2d^\star_{100p} \times 1/2d^\star_{010p}$ square mesh which corresponds to the $2a_p^{(1)} \times 2a_p^{(2)}$ superlattice cell;

(") the streaks of very weak intensity marked by single arrowheads in Fig. 3d which intersects the $(hk0)^\star$ section of Fig. 2 at the centres of the $1/4d^\star_{100p} \times 1/2d^\star_{010p}$ rectangular mesh. These streaks are based on the centred $4a_p^{(1)} \times 2a_p^{(2)}$ plane lattice cell.

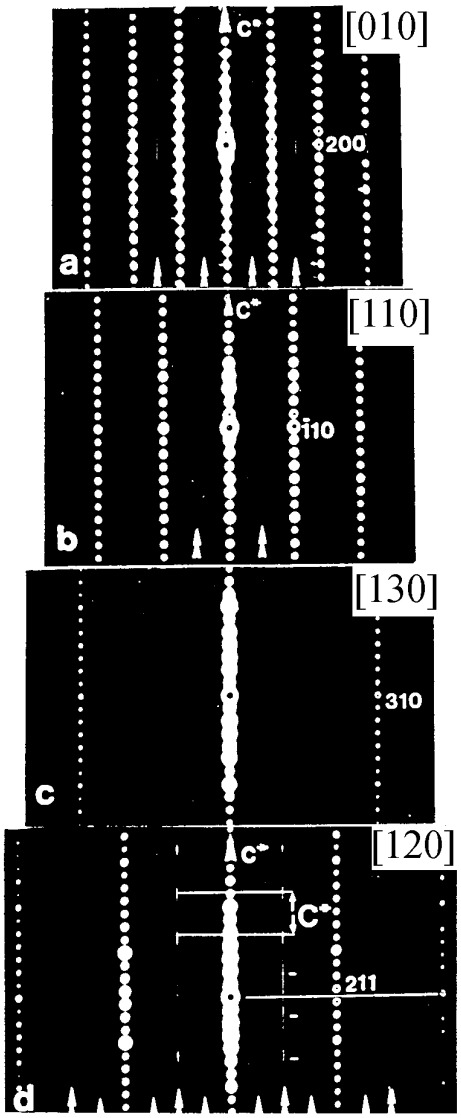

Fig. 3. Series of EDPs of the $RE_2(Sr_{0.20}Ba_{0.65}Nd_{0.15})_2GaCu_2O_9$ *compound: (a) the* $[010]_p$ *zone; (b) the* $[110]_p$ *zone; (c) the* $[\bar{1}30]_p$ *zone; (d) the* $[\bar{1}20]_p$ *zone. Black dots mark the basic spots which are labelled in perovskite notation; double arrowheads in (a) and (d) mark the diffuse streaks which belong to the* $2a_p \times 2a_p$ *mesh; single arrowheads in (d) mark the very weak diffuse streaks which belong to the centred* $4a_p \times 2a_p$ *mesh. Period of streak intensity modulation* $C^\star$ *is indicated in (d), along the intensity maxima positions.*

The family of diffuse streaks based on the $2a_p \times 2a_p$ lattice is of particular interest because of its prominent intensity modulation visible in Figs. 3a and d; the streaks are absent

in Fig. 3b due to extinction; the period of this sinusoidal modulation is $C^\star \approx 6.4c_p^\star$. The positions of intensity maxima and minima along $c^\star$ can not be unambiguously determined from Fig. 3a where both families of streaks overlap, but the minima are clearly discerned at $l = 0$ in the $[120]_p$ zone pattern of Fig. 3d, where the two families of streaks appear separated.

4. Model and discussion

The family of streaks with the intensity modulation in reciprocal space is a well known indication [17] of the existing bi-layer configuration within the unit cell in direct space. The investigation of this diffuse intensity allows one to determine:

(i) which of the plane-layer substructures exhibits additional ordering, and

(ii) what are the symmetry restrictions on the ordering scheme in these planes.

All diffraction features can be accounted for by a simple scheme of composition ordering of 3Ba and 1Sr atoms on the $2a_p \times 2a_p$ lattice in the $(Sr_{0.25}Ba_{0.75})O$ layers as shown in Fig. 4 (for simplicity, the fraction of Nd atoms is not considered).

Let the contribution to the scattering amplitude of 3Ba+1Sr atoms, arranged on a $2a_p \times 2a_p$ cell in one layer, be written as:

$$F_g^{2\times 2} = f^{(Sr)}\left[1 + \Delta f\left(e^{\pi i\vec{g}\cdot\vec{a}'} + e^{\pi i\vec{g}\cdot\vec{b}'} + e^{\pi i\vec{g}\cdot(\vec{a}'+\vec{b}')}\right)\right]$$

where $\Delta f = f^{(Ba)} - f^{(Sr)}$, $\vec{a}' = 2\vec{a}_p^{(1)}$ and $\vec{b}' = 2\vec{a}_p^{(2)}$, while $\vec{g}$ is the diffraction vec-

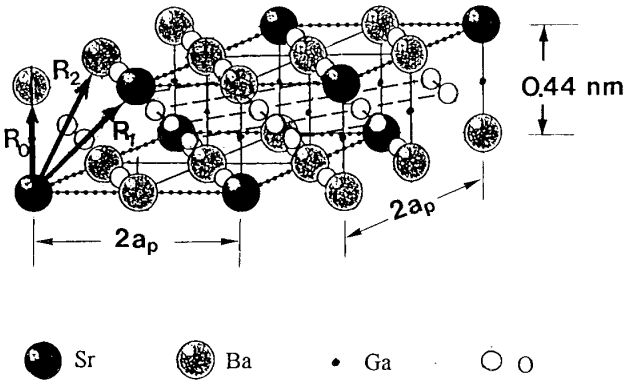

Fig. 4. Scheme of compositional ordering in the $(Sr_{0.25}Ba_{0.75})O$ *planes (RS-type layers) of the* (Sr/Ba)O-GaO-(Sr/Ba)O *lamella in* $RE_2(Sr_{0.20}Ba_{0.65}Nd_{0.15})_2GaCu_2O_9$ *structure. The broken lines indicate the* $2a_p \times 2a_p$ *square units in the bottom and top planes. Vectors* $\vec{R}_i$ *denote the correlation vectors.*

tor. The additional scattering amplitude from the whole family of RS-layers is:

$$F_g^{(L)} = F_g^{2\times 2} \sum_{jl} \mathrm{e}^{2\pi \mathrm{i} \vec{g}\cdot\vec{r}'_{jl}},$$

where the summation index j runs over all layers and index l over all (a',b') sites in one layer. In the case when these sites are related by a displacement vector $\vec{R}$ in the pair of adjacent RS-layers, the corresponding structure factor can be written as:

$$F_g^{(BL)} = F_g^{2\times 2} \left(1 + \mathrm{e}^{2\pi \mathrm{i} \vec{g}\cdot\vec{R}}\right) \sum_{j'l} \mathrm{e}^{2\pi \mathrm{i} \vec{g}\cdot\vec{r}'_{j'l}},$$

where the index j' runs now over all bi-layers. The vector $\vec{R}$ relating the two layers in a bi-layer can be decomposed in two components: $\vec{R} = \vec{R}_\perp + \vec{R}_\parallel$, where $\vec{R}_\perp$ $(= \delta\vec{c})$ is perpendicular to the layers (δ denotes fraction of the c-spacing), and the component $\vec{R}_\parallel$ is parallel to the layers. The intensity distribution along the streaks in the corresponding diffraction pattern is given by a sinusoidal modulation with the period $1/\delta$ and phase $\alpha_g = 2\pi\vec{g}_\parallel \cdot \vec{R}_\parallel$:

$$I_g = 2[1 + \cos 2\pi(\delta l + \alpha_g)] \;\; |F_g^{2\times 2} \sum_{j'l} \mathrm{e}^{2\pi \mathrm{i} \vec{g}\cdot\vec{r}'_{j'l}}|^2,$$

where the reciprocal period $1/\delta = C^\star$ (in $c^\star$ units) indicates that the layers exhibiting additional ordering (responsible for this modulation) must be separated by $\delta = C$. The phase α_g indicates a relative shift of two configurations of ordered $2a_p \times 2a_p$ meshes between adjacent layers. Since the intensity of the streaks have a minimum at $l = 0$ in Fig. 3d, vertical stacking of the $2a_p \times 2a_p$ meshes in the $(Sr_{0.25}Ba_{0.75)}O$ bi-layers is forbidden. The relative displacement vector $\vec{R}_1$ in Fig. 4 represents one possible bi-layer configuration of 3Ba and 1Sr atoms on the $2a_p \times 2a_p$ lattice in the $(Ba_{0.75}Sr_{0.25})O$ layer below and above the GaO-chain plane. All other configurations with the non-zero component $\vec{R}_\parallel$ of the displacement vector ($\vec{R}_2$ in Fig. 4) are also consistent with the intensity minima at $l = 0$; vertical stacking $\vec{R}_0 = \delta\vec{c}$ would have $\alpha_g = 0$, thus giving a maximum at $l = 0$. The stacking of bi-layer in successive slabs is correlated by one of four vectors: $\vec{S} = \pm 1/2\vec{a}_p^{(1)} \pm 1/2\vec{a}_p^{(2)} + 1/2\vec{c}_p$, thus generating the observed extinction conditions $(h + k = 2/\mathrm{mod}\ 4)$ for the superlattice spots, indicated by small arrows in Fig. 2, and for the streaks indicated by double arrowheads in Fig. 3b. The streaking along the $c^\star$-axis reveals a high degree of plane stacking disorder which is due to four possible vectors $\vec{S}$ correlating the bi-layers in successive slabs.

The HREM imaging of the Ga-1222C structure along the $[100]_p$ and $[210]_p$ zones, in Figs. 5a and b, respectively, supports this model. Namely, the proposed scheme for RS-layer ordering is a rather weak modification of the average basic structure. Therefore, imaging along the $[100]_p$ zone in Fig. 5a represents only the basic Ga-1222C structure with no certain indication of additional $2a_p \times 2a_p$ plane-structure in the RS-bi-layers. This RS-bi-layer ordering is revealed only by the "oblique zone" imaging [18] along the $[210]_p$ zone of fig. 5b, a weak variation of dot brightness in the pair of bright fringes marked by

arrows. The fringe separation $C = 0.44$ nm fully agrees with the streak modulation period $C^{\star} = (1/0.44)\ \mathrm{nm}^{-1}$ in the corresponding diffraction pattern of Fig. 3d.

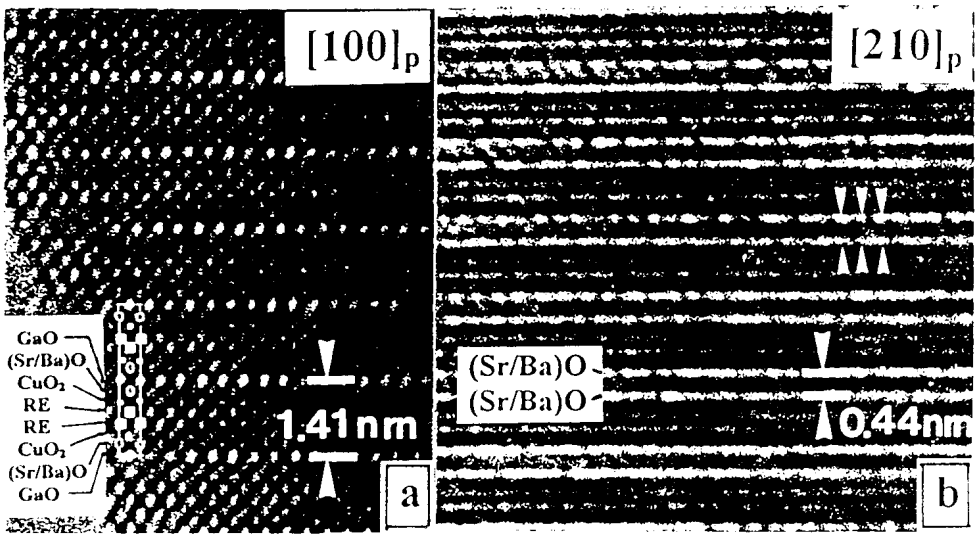

Fig. 5. HREM imaging of the $RE_2(Sr_{0.20}Ba_{0.65}Nd_{0.15})_2GaCu_2O_9$ *structure: (a) along the* $[100]_p$ *zone and; (b) along the* $[210]_p$ *zone. The layers of basic structure are indicated in the legend of (a). The RS-type bi-layers* (Sr/Ba)O...(Sr/Ba) *are marked by arrows in (b).*

5. Conclusions

Compositional ordering of Ba and Sr atoms is detected in $(Sr_{0.20}Ba_{0.65}Nd_{0.15})O$ ... $(Sr_{0.20}Ba_{0.65}Nd_{0.15})O$ ... bi-layers of the Ga-1222C basic structure; the bi-layers are of the RS-type with the $2a_p \times 2a_p$ superstructure. This ordering in the RS-bi-layers takes place on top of the meandering chain arrangement in the GaO-layers of the $(RE)_2(Sr_{0.85-x}Ba_xNd_{0.15})_2GaCu_2O_{9+\delta}$ compound for $x = 0.65$. The ordering seems to be only a weak, local modification of the basic Ga-1222C structure. Namely, the absence of vertical stacking of the $2a_p \times 2a_p$ configuration in two (Ba/Sr)O planes of a single bi-layer can locally accommodate for the 4-fold symmetry of the CuO_2-plane layers and the 2-fold symmetry of the meandering chains in the GaO-layers based on the $4a_p \times 2a_p \times c_p$ superlattice. Due to twinning in the GaO-chain layers, and the plane stacking disorder of the adjacent (Ba/Sr)O...(Ba/Sr)O

bi-layers in successive slabs, the symmetry of this structure is apparently enhanced to the tetragonal symmetry of the average Ga-1222 structure.

Acknowledgements

O. Milat is grateful to G. Van Tendeloo and S. Amelinckx of EMAT-RUCA-department at the University of Antwerp (Belgium) for the fruitful collaboration, and to A. J. Wright

and C. Greaves of School of Chemistry at the University of Birmingham (U.K.) for providing the samples.

This work has been financially supported by the Ministry of Science and Technology of the Republic of Croatia, and partially by the EC EPSRC program.

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UREDJENJE (Ba/Sr)O-DVOSLOJEVA U SUPRAVODLJIVOM KUPRATU $RE_2(Ba/Sr)_2GaCu_2O_9$

Strukturno uređenje (Ba/Sr/Nd)O dvoslojeva u supravodljivom kupratu sastava $RE_2(Ba/Sr)_2GaCu_2O_9$ istraživano je pomoću elektronske mikroskopije i difrakcije. Osim prosječne tetragonske strukture na osnovi slojevite perovskitske tetragonske ćelije $a_p \times a_p \times c_p$, i nadstrukture meandrirajućih lanaca u GaO-ravninama s ortorombskom ćelijom $4a_p \times 2a_p \times c_p$, nađeno je dodatno uređenje u parovima (Ba/Sr/Nd)O-...-(Ba/Sr/Nd)O ravnina. Predložen je model uređenja 3Ba i 1Sr kationa unutar $2a_p \times 2a_p$ dvodimenzijske ćelije u svakoj (Ba/Sr/Nd)O ravnini. Ovo unutar-ravninsko uređenje popraćeno je među-ravninskim neredom u nizu slaganja slojeva. Simetrija 4-reda, koja je svojstvena prosječnoj tetragonskoj strukturi ostaje sačuvana, uz podvostručenje parametara rešetke u (a, b) ravnini. Opaženo uređenje unutar (Ba/Sr/Nd)O dvoslojeva ovog supravodljivog kuprata nema jaki utjecaj na simetriju osnovne strukture, ali može biti izvor lokalne anizotropije u CuO_2-ravninama.